

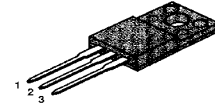
FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 25 μ A (Max.) @ $V_{DS} = 600V$
- Low $R_{DS(ON)}$: 0.646 Ω (Typ.)

$$BV_{DSS} = 600 V$$

$$R_{DS(on)} = 0.8 \Omega$$

$$I_D = 5.1 A$$

TO-220F

1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

| Symbol | Characteristic | Value | Units |
|----------------|--|--------------|------------|
| V_{DSS} | Drain-to-Source Voltage | 600 | V |
| I_D | Continuous Drain Current ($T_C=25^\circ C$) | 5.1 | A |
| | Continuous Drain Current ($T_C=100^\circ C$) | 3.2 | |
| I_{DM} | Drain Current-Pulsed ① | 36 | A |
| V_{GS} | Gate-to-Source Voltage | ± 30 | V |
| E_{AS} | Single Pulsed Avalanche Energy ② | 709 | mJ |
| I_{AR} | Avalanche Current ① | 5.1 | A |
| E_{AR} | Repetitive Avalanche Energy ① | 5 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | 3.0 | V/ns |
| P_D | Total Power Dissipation ($T_C=25^\circ C$) | 50 | W |
| | Linear Derating Factor | 0.4 | |
| T_J, T_{STG} | Operating Junction and Storage Temperature Range | - 55 to +150 | $^\circ C$ |
| T_L | Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds | 300 | |

Thermal Resistance

| Symbol | Characteristic | Typ. | Max. | Units |
|-----------------|---------------------|------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case | -- | 2.5 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction-to-Ambient | -- | 62.5 | |

Electrical Characteristics (T_C=25°C unless otherwise specified)

| Symbol | Characteristic | Min. | Typ. | Max. | Units | Test Condition |
|---------------------|---|------|------|------|-------|---|
| BV _{DSS} | Drain-Source Breakdown Voltage | 600 | -- | -- | V | V _{GS} =0V, I _D =250μA |
| ΔBV/ΔT _J | Breakdown Voltage Temp. Coeff. | -- | 0.66 | -- | V/°C | I _D =250μA See Fig 7 |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | -- | 4.0 | V | V _{DS} =5V, I _D =250μA |
| I _{GSS} | Gate-Source Leakage, Forward | -- | -- | 100 | nA | V _{GS} =30V |
| | Gate-Source Leakage, Reverse | -- | -- | -100 | | V _{GS} =-30V |
| I _{DSS} | Drain-to-Source Leakage Current | -- | -- | 25 | μA | V _{DS} =600V |
| | | -- | -- | 250 | | V _{DS} =480V, T _C =125°C |
| R _{DS(on)} | Static Drain-Source On-State Resistance | -- | -- | 0.8 | Ω | V _{GS} =10V, I _D =2.55A ④ |
| g _{fs} | Forward Transconductance | -- | 6.23 | -- | Ω | V _{DS} =50V, I _D =2.55A ④ |
| C _{iss} | Input Capacitance | -- | 1750 | 2270 | pF | V _{GS} =0V, V _{DS} =25V, f = 1MHz See Fig 5 |
| C _{oss} | Output Capacitance | -- | 190 | 220 | | |
| C _{rss} | Reverse Transfer Capacitance | -- | 78 | 90 | | |
| t _{d(on)} | Turn-On Delay Time | -- | 20 | 50 | ns | V _{DD} =300V, I _D =10A, R _G =6.2Ω See Fig 13 ④⑤ |
| t _r | Rise Time | -- | 23 | 55 | | |
| t _{d(off)} | Turn-Off Delay Time | -- | 85 | 180 | | |
| t _f | Fall Time | -- | 30 | 70 | | |
| Q _g | Total Gate Charge | -- | 74 | 95 | nC | V _{DS} =480V, V _{GS} =10V, I _D =10A See Fig 6 & Fig 12 ④⑤ |
| Q _{gs} | Gate-Source Charge | -- | 12 | -- | | |
| Q _{gd} | Gate-Drain("Miller ") Charge | -- | 35.4 | -- | | |

Source-Drain Diode Ratings and Characteristics

| Symbol | Characteristic | Min. | Typ. | Max. | Units | Test Condition |
|-----------------|---------------------------|------|------|------|-------|---|
| I _S | Continuous Source Current | -- | -- | 5.1 | A | Integral reverse pn-diode in the MOSFET |
| I _{SM} | Pulsed-Source Current ① | -- | -- | 36 | | |
| V _{SD} | Diode Forward Voltage ④ | -- | -- | 1.4 | V | T _J =25°C, I _S =5.1A, V _{GS} =0V |
| t _{rr} | Reverse Recovery Time | -- | 440 | -- | ns | T _J =25°C, I _F =10A |
| Q _{rr} | Reverse Recovery Charge | -- | 4.7 | -- | μC | dI _F /dt=100A/μs ④ |

Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=50mH, I_{AS}=5.1A, V_{DD}=50V, R_G=27Ω, Starting T_J=25°C
- ③ I_{SD} ≤ 10A, di/dt ≤ 50A/μs, V_{DD} < BV_{DSS}, Starting T_J=25°C
- ④ Pulse Test : Pulse Width = 250 μs, Duty Cycle ≤ 2%
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

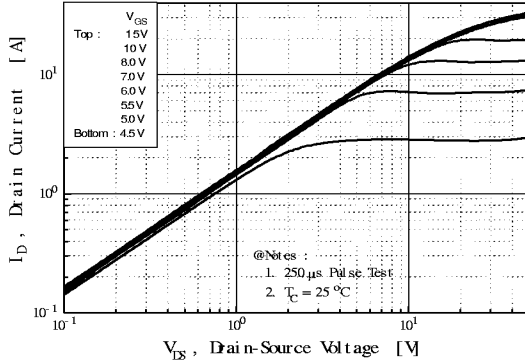


Fig 2. Transfer Characteristics

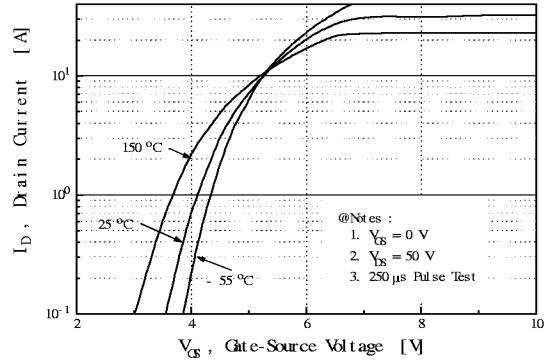


Fig 3. On-Resistance vs. Drain Current

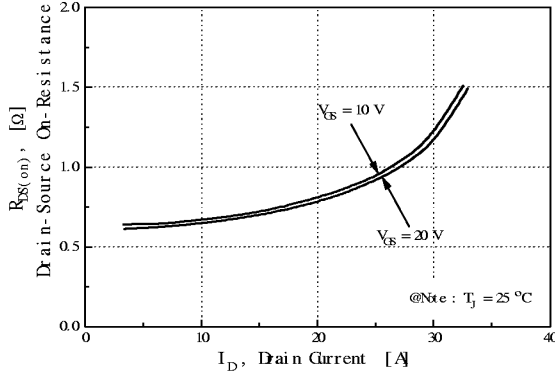


Fig 4. Source-Drain Diode Forward Voltage

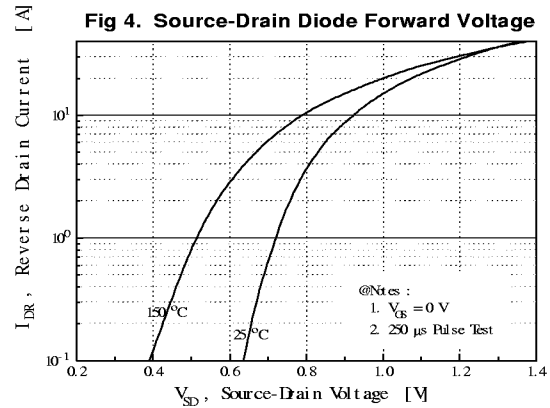


Fig 5. Capacitance vs. Drain-Source Voltage

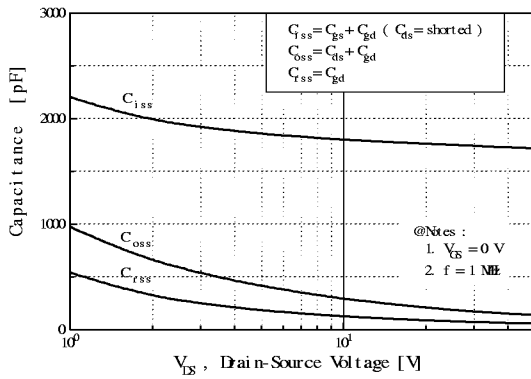
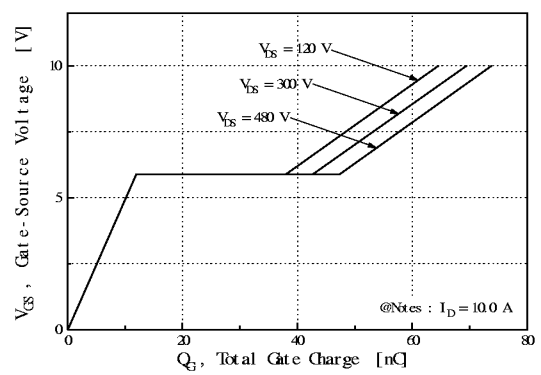
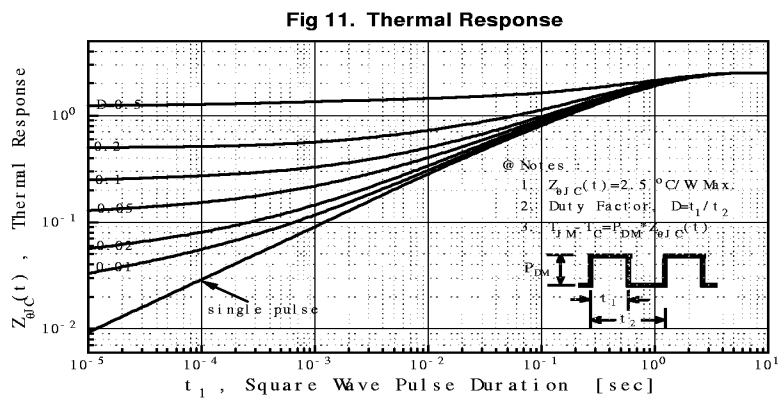
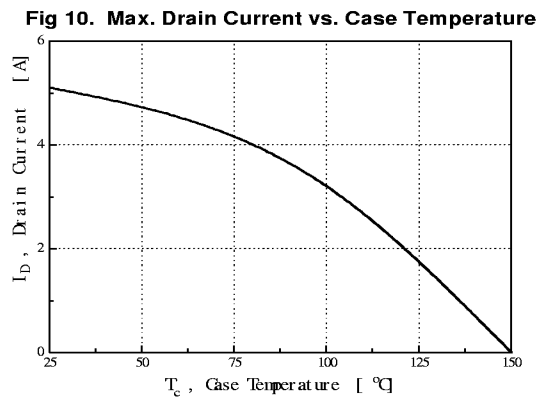
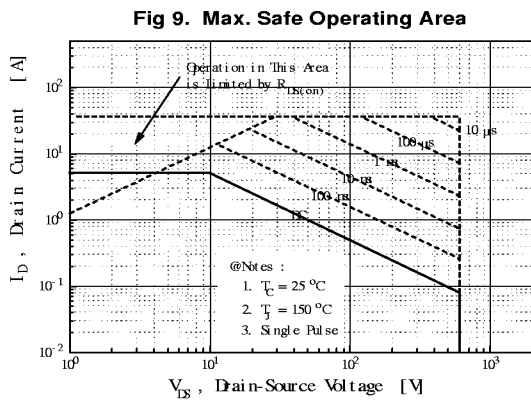
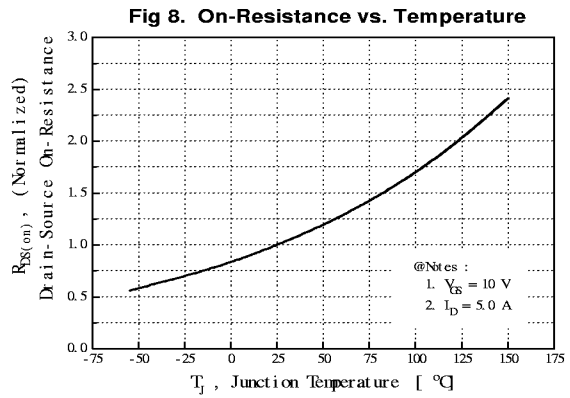
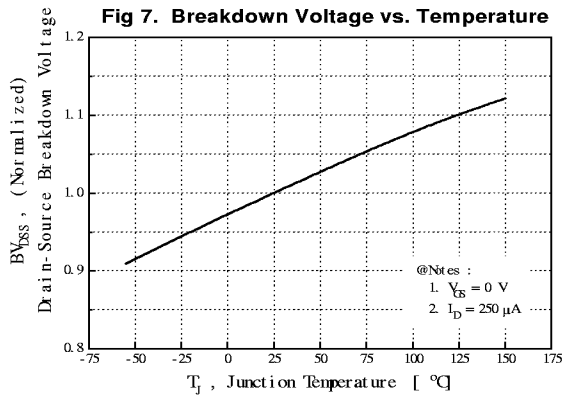


Fig 6. Gate Charge vs. Gate-Source Voltage



SSS10N60A

N-CHANNEL POWER MOSFET



FAIRCHILD
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Fig 12. Gate Charge Test Circuit & Waveform

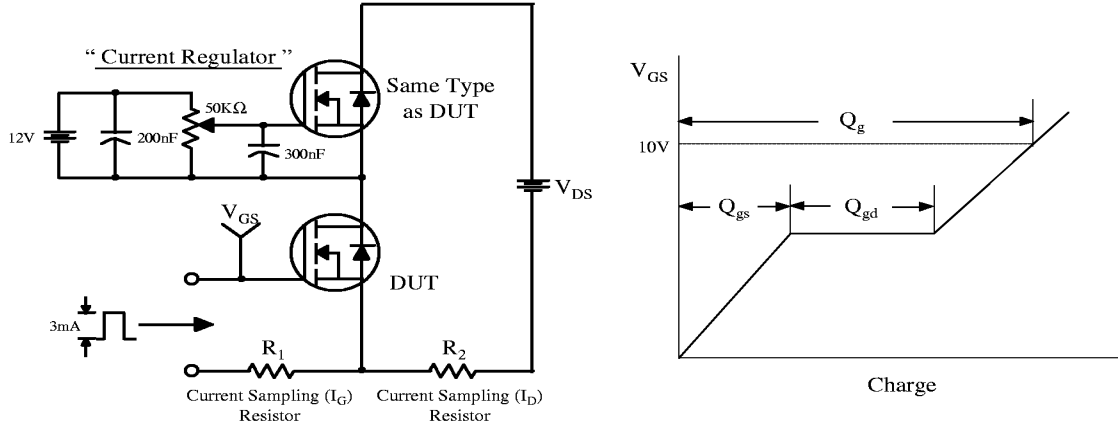


Fig 13. Resistive Switching Test Circuit & Waveforms

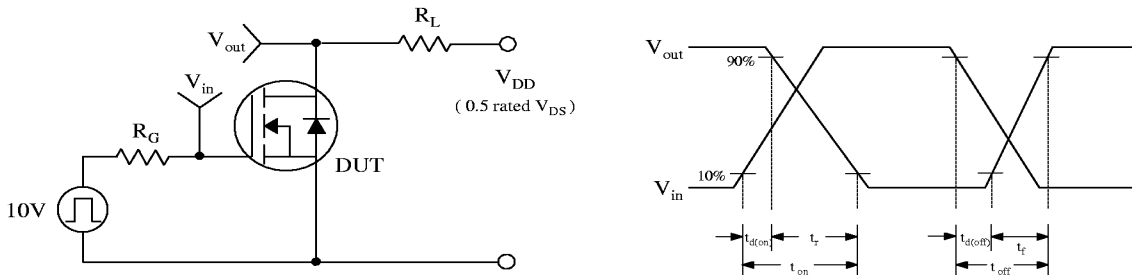


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

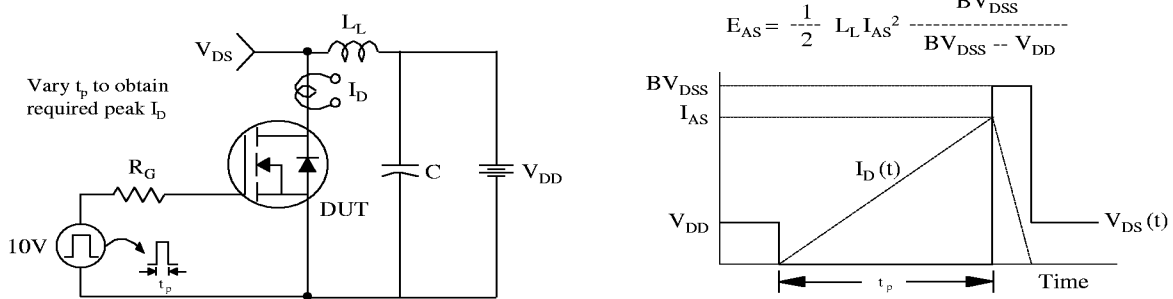


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

